

HIGH ASPECT RATIO ETCH USING MODULATION OF RF POWERS OF VARIOUS FREQUENCIES

ABSTRACT OF THE DISCLOSURE

5 A method for etching a high aspect ratio feature through a mask into a layer to
be etched over a substrate is provided. The substrate is placed in a process chamber,
which is able to provide RF power at a first frequency, a second frequency different
than the first frequency, and a third frequency different than the first and second
frequency. An etchant gas is provided to the process chamber. A first etch step is
10 provided, where the first frequency, the second frequency, and the third frequency are
at power settings for the first etch step. A second etch step is provided, where the first
frequency, the second frequency, and the third frequency are at a different power
setting.

15